

Medium Power Thyristors (Stud Version), 10 A



TO-208AA (TO-48)

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High di/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- RoHS compliant
- Designed and qualified for industrial and consumer level



PRODUCT SUMMARY

$I_{T(AV)}$	50 A
-------------	------

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		10	A
	T_C	85	°C
$I_{T(RMS)}$		25	A
I_{TSM}	50 Hz	225	A
	60 Hz	240	
I^2t	50 Hz	255	A ² s
	60 Hz	233	
V_{DRM}/V_{RRM}		100 to 1200	V
t_q	Typical	110	μs
T_J		- 65 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
10RIA	10	100	150	20
	20	200	300	10
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if di/dt does not exceed 20 A/ μ s

⁽²⁾ For voltage pulses with $t_p \leq 5$ ms

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			10	A	
					85	°C	
Maximum RMS on-state current	I _{T(RMS)}				25	A	
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	225	A	
		t = 8.3 ms			240		
		t = 10 ms	100 % V _{RRM} reapplied		190		
		t = 8.3 ms			200		
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied			255	A ² s
		t = 8.3 ms				233	
		t = 10 ms	100 % V _{RRM} reapplied			180	
		t = 8.3 ms				165	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			2550	A ² √s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)}), T _J = T _J maximum			1.10	V	
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.39		
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)}), T _J = T _J maximum			24.3	mΩ	
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			16.7		
Maximum on-state voltage	V _{TM}	I _{pk} = 32 A, T _J = 25 °C, t _p = 10 ms sine pulse			1.75	V	
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load			130	mA	
Typical latching current	I _L				200		



SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum rate of rise of turned-on current	di/dt	T _J = T _J maximum, V _{DM} = Rated V _{DRM} Gate pulse = 20 V, 15 Ω, t _p = 6 μs, t _r = 0.1 μs maximum I _{TM} = (2 x rated di/dt) A	200	A/μs
			180	
			160	
			150	
Typical turn-on time	t _{gt}	T _J = 25 °C, at rated V _{DRM} /V _{RRM} , T _J = 125 °C	0.9	μs
Typical reverse recovery time	t _{rr}	T _J = T _J maximum, I _{TM} = I _{T(AV)} , t _p > 200 μs, di/dt = - 10 A/μs	4	
Typical turn-off time	t _q	T _J = T _J maximum, I _{TM} = I _{T(AV)} , t _p > 200 μs, V _R = 100 V, di/dt = - 10 A/μs, dV/dt = 20 V/μs linear to 67 % V _{DRM} , gate bias 0 V to 100 W	110	

Note

- t_q = 10 μs up to 600 V, t_q = 30 μs up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 100 % rated V _{DRM}	100	V/μs
		T _J = T _J maximum linear to 67 % rated V _{DRM}	300 ⁽¹⁾	

Note

- ⁽¹⁾ Available with: dV/dt = 1000 V/μs, to complete code add S90 i.e. 10RIA120S90

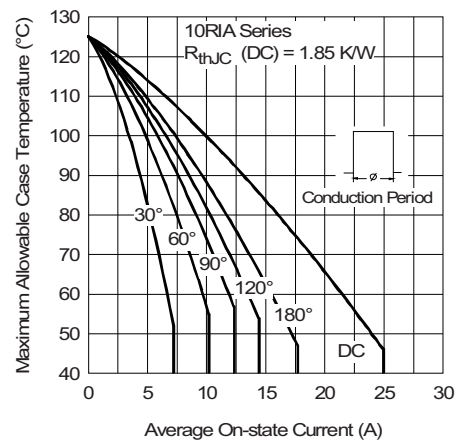
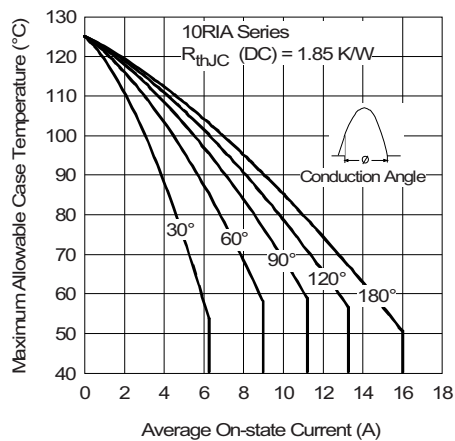
TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T _J = T _J maximum	8.0	W
Maximum average gate power	P _{G(AV)}		2.0	
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum	1.5	A
Maximum peak negative gate voltage	-V _{GM}	T _J = T _J maximum	10	V
DC gate current required to trigger	I _{GT}	T _J = - 65 °C	90	mA
		T _J = 25 °C	60	
		T _J = 125 °C	35	
DC gate voltage required to trigger	V _{GT}	T _J = - 65 °C	3.0	V
		T _J = 25 °C	2.0	
		T _J = 125 °C	1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	2.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction and storage temperature range	T_J, T_{Stg}		- 65 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.85	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.35	
			TO NUT	TO DEVICE
Mounting torque		Lubricated threads (Non-lubricated threads)	20 (27.5)	25
			0.23 (0.32)	0.29
			2.3 (3.1)	2.8
Approximate weight			14	g
			0.49	oz.
Case style		See dimensions - link at the end of datasheet	TO-208AA (TO-48)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.44	0.32	$T_J = T_J$ maximum	K/W
120°	0.53	0.56		
90°	0.68	0.75		
60°	1.01	1.05		
30°	1.71	1.73		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



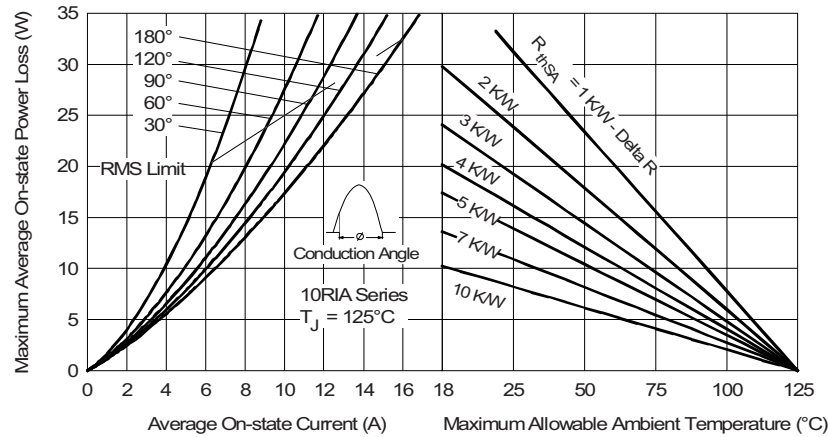


Fig. 3 - On-State Power Loss Characteristics

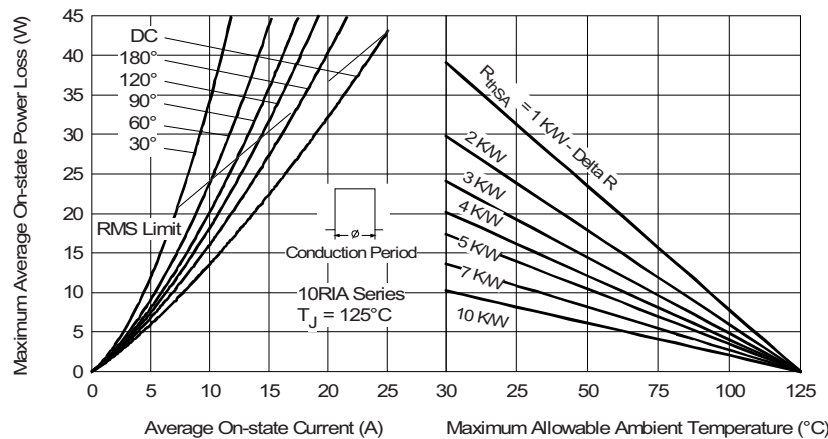


Fig. 4 - On-State Power Loss Characteristics

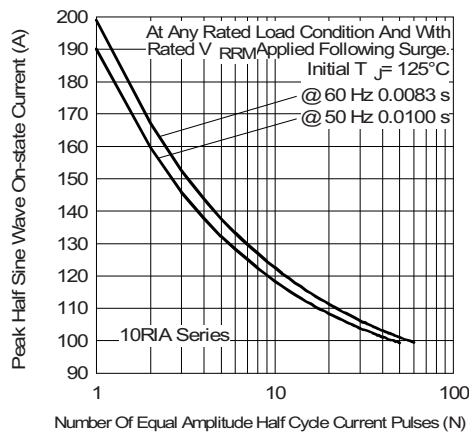


Fig. 5 - Maximum Non-Repetitive Surge Current

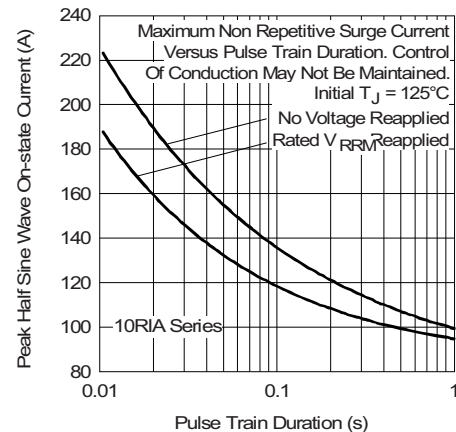


Fig. 6 - Maximum Non-Repetitive Surge Current

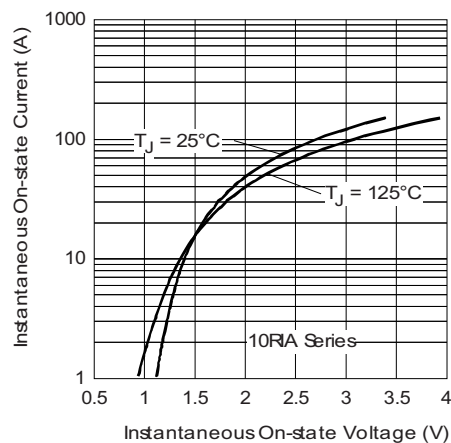


Fig. 7 - Forward Voltage Drop Characteristics

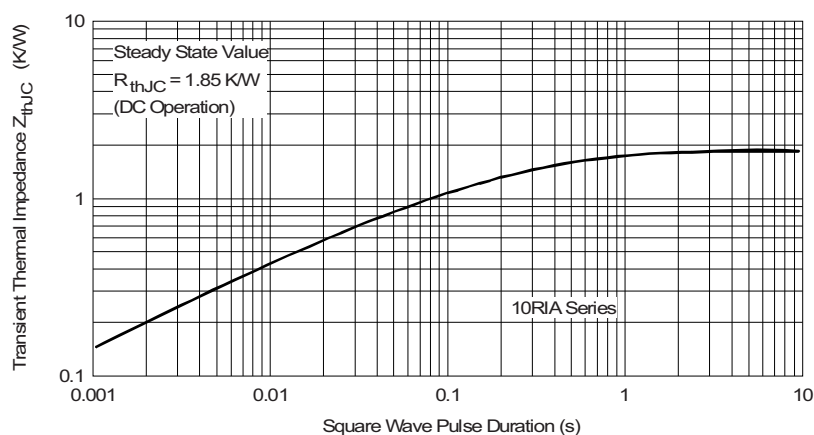


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

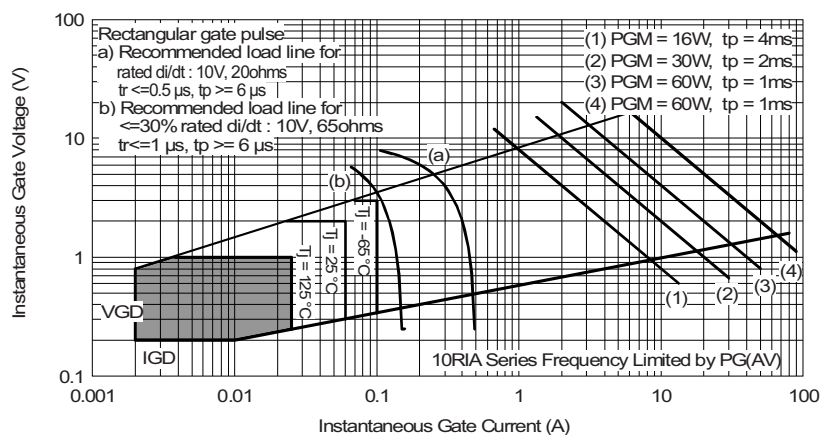


Fig. 9 - Gate Characteristics



ORDERING INFORMATION TABLE

10	RIA	120	M	S90
----	-----	-----	---	-----

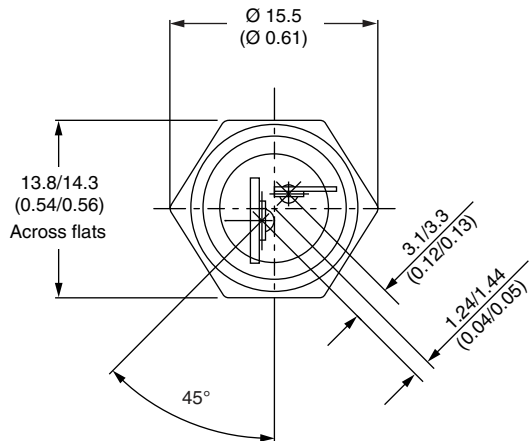
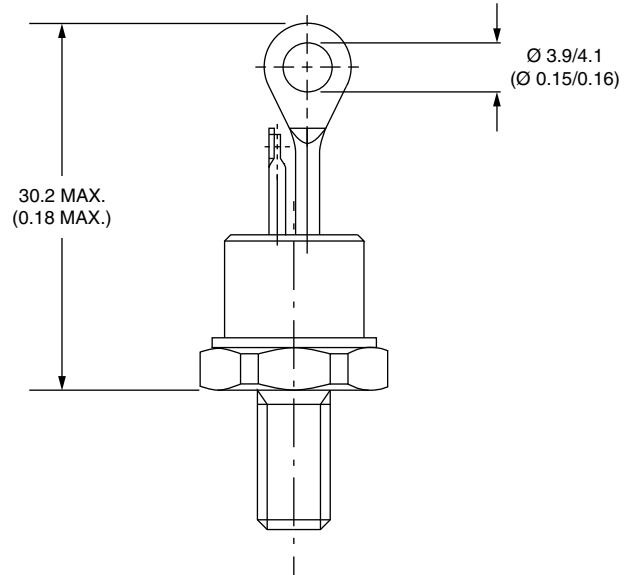
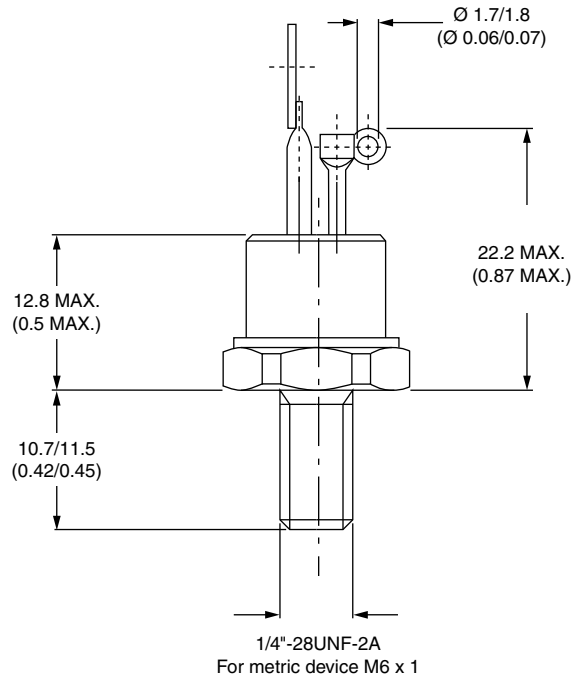
1 2 3 4 5

- 1** - Current code
- 2** - Essential part number
- 3** - Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 4** - None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
M = Stud base TO-208AA (TO-48) M6 x 1
- 5** - Critical dV/dt:
None = 300 V/ μ s (standard value)
S90 = 1000 V/ μ s (special selection)

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95333

TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)





Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru